

Effect of hydrostatic pressure, temperature, and doping

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Atomic Diffusion With Strain and Injection. Materials Research Society Symposia Proceedings, 1990, 184, 165.	0.1	2
2	Pressure-Enhanced Solid Phase Epitaxy: Implications for Point Defect Mechanisms. Materials Research Society Symposia Proceedings, 1990, 205, 33.	0.1	0
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